

UNISONIC TECHNOLOGIES CO., LTD

MMBTA94

PNP SILICON TRANSISTOR

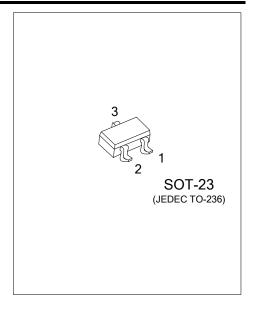
HIGH VOLTAGE TRANSISTOR

■ FEATURES

- * Collector-Emitter Voltage: V_{CEO} = -400V
- * Collector Dissipation: P_{C(MAX)} = 350mW
- * Low Collector-Emitter Saturation Voltage

APPLICATIONS

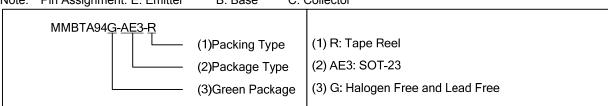
- * Telephone Switching
- * High Voltage Switch



ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			Dealing	
		1	2	3	Packing	
MMBTA94G-AE3-R	SOT-23	E	В	С	Tape Reel	

Note: Pin Assignment: E: Emitter B: Base C: Collector



MARKING



www.unisonic.com.tw 1 of 3

■ ABSOLUTE MAXIMUM RATING (T_A=25°C unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	-400	V
Collector-Emitter Voltage	V _{CEO}	-400	V
Emitter-Base Voltage	V _{EBO}	-6	V
Collector Current	Ic	-300	mA
Collector Dissipation (Ta=25°C)	Pc	350	mW
Junction Temperature	TJ	+150	°C
Storage Temperature	T _{STG}	-40~+150	°C

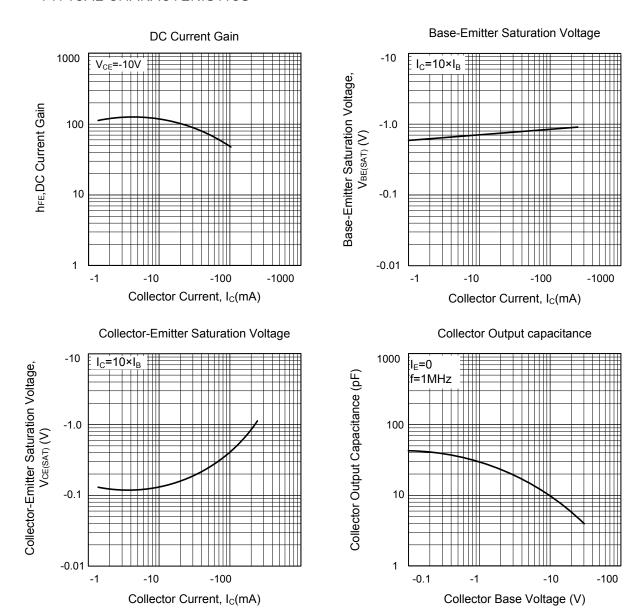
Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_CBO	$I_C = -100 \mu A, I_E = 0$	-400			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I_C = -1mA, I_B =0	-400			V
Collector-Emitter Breakdown Voltage	BV _{CES}	$I_{C} = -100 \mu A, V_{BE} = 0$	-400			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I _E = -100μA, I _C =0	-5			V
Collector Cut-off Current	I _{CBO}	V _{CB} = -300V, I _E =0			-100	nA
Collector Cut-off Current	I _{CES}	V _{CB} = -400V, V _{BE} =0			-1	μΑ
Emitter Cut-off Current	I _{EBO}	V _{EB} = -4V, I _C =0			100	nA
DC Current Gain (Note)	h _{FE}	V_{CE} = -10V, I_{C} = -1mA	60			
		V _{CE} = -10V, I _C = -10mA	70		300	
		V_{CE} = -10V, I_C = -50mA	70			
		V _{CE} = -10V, I _C = -100mA	40			
Collector-Emitter Saturation Voltage	VCE(SAT)	I_C = -10mA, I_B = -1mA			-0.20	V
		I_C = -50mA, I_B = -5mA			-0.5	V
Base-Emitter Saturation Voltage	V _{BE(SAT)}	I _C = -10mA, I _B = -1mA			-0.75	V
Output Capacitance	Cob	V _{CB} = -20V,I _E =0, f =1MHz			7	pF

Note: Pulse test: PW<300µs, Duty Cycle<2%

■ TYPICAL CHARACTERISTICS



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by Unisonic manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H MMBT-2369-TR BC546/116 BC557/116 BSW67A NJVMJD148T4G NTE123AP-10 NTE153MCP NTE16

NTE195A NTE92 C4460 2N4401-A 2N6728 2SA1419T-TD-H 2SA2126-E 2SB1204S-TL-E 2SC2712S-GR,LF 2SC5488A-TL-H

2SD2150T100R SP000011176 2N2369ADCSM 2N2907A 2N3904-NS 2N5769 2SC2412KT146S 2SD1816S-TL-E CPH6501-TL-E

MCH4021-TL-E MJE340 US6T6TR NJL0281DG 732314D CPH3121-TL-E CPH6021-TL-H 873787E IMZ2AT108 UMX21NTR

MCH6102-TL-E NJL0302DG 2N3583 30A02MH-TL-E NSV40301MZ4T1G NTE13 NTE26 NTE282 NTE323 NTE350 NTE81